

Our Company

Custom & OEM Solutions

Standard Products

Technology Corner

OSI Optoelectronics Family

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Overview

Parametric Product Search

Silicon Photodiodes

- + General Purpose Photodiodes
- + High Speed Silicon Photodiodes
- [UV Enhanced Photodiodes](#)

[Overview](#)

Inversion Layer Photodiodes

Planar Diffused Photodiodes

Planar Diffused IR Suppressed Photodiode

- + X-Ray and Radiation Detectors
- + Photodiode Arrays
- + Two Color Sandwich Detectors
- + Nd-YAG Optimized Photodiodes
- + Avalanche Photodiodes
- + Photodiode Amplifier Hybrids
- + Photodiode Filter Assembly
- + Solderable Chip Photodiodes
- + Position Sensing Detectors
- + Plastic Encapsulated Detectors

InGaAs Photodiodes

GaAs Photodiodes

New Products

Discontinued Products

## UV Enhanced Photodiodes

Generally sensitive between 200 to 1100nm these detectors are typically packaged with quartz or UV transmissive glass window. They exhibit low dark current and can be reverse biased for lower capacitance and faster rise time performance.



### Inversion Layer Photodiodes

Inversion Layer Photodiodes exhibit 100% internal quantum efficiency and are well suited for low intensity light measurements. [View Products & Descriptions](#)



### Planar Diffused Photodiodes

Planar Diffused photodiodes offer lower capacitance and higher risetimes compared to the Inversion Layer photodiodes. These devices also exhibit linearity of photocurrent up to higher light outputs. [View Products & Descriptions](#)



### Planar Diffused IR Suppressed Photodiodes

Planar Diffused photodiodes offer lower capacitance and higher risetimes compared to the Inversion Layer photodiodes. These devices also exhibit linearity of photocurrent up to higher light outputs. The IR sensitivity of these devices is suppressed to minimize ambient light interference. [View Products & Descriptions](#)

[Product Overview](#)  
[Product & Specifications](#)

Overview

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Silicon Photodiodes

- + General Purpose Photodiodes
- + High Speed Silicon Photodiodes
- UV Enhanced Photodiodes

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## Inversion Layer Photodiodes

Inversion Layer, Metal & Plastic Packages

 [Download Datasheet](#)    [Technical Support](#)    [Email This Page](#)

OSI Optoelectronics offers two distinct families of UV enhanced silicon photodiodes. Inversion channel series and planar diffused series. Both families of devices are especially designed for low noise detection in the UV region of electromagnetic spectrum.

Inversion layer structure UV enhanced photodiodes exhibit 100% internal quantum efficiency and are well suited for low intensity light measurements. They have high shunt resistance, low noise and high breakdown voltages. The response uniformity across the surface and quantum efficiency improves with 5 to 10 volts applied reverse bias. Photocurrent non-linearity sets in at lower photocurrents for inversion layer devices compared to the diffused ones. Below 700nm, their responsivities vary little with temperature.






### Product Applications







- Pollution Monitoring
- Medical Instrumentation
- UV Exposure Meters
- Spectroscopy
- Water Purification
- Fluorescence

### Product Features




- Inversion series: 100% Internal QE
- Ultra High Shunt Resistance
- Excellent UV Response

### Inversion Layer, Metal Package

Model Number	Active Area	Active Area Dimensions	Responsivity @ 254nm	Capacitance	Shunt Resistance	Rise Time	Package	Click Image to Zoom
UV-001	0.8 mm <sup>2</sup>	1.0 F mm	0.14 A/W	60 pF	500 MΩ	0.2 μs	5 / TO-5	
UV-005	5.1 mm <sup>2</sup>	2.54 Φ mm	0.14 A/W	300 pF	200 MΩ	0.9 μs	5 / TO-5	
UV-015	15 mm <sup>2</sup>	3.05 x 3.81 mm	0.14 A/W	800 pF	100 MΩ	2 μs	5 / TO-5	
UV-20	20 mm <sup>2</sup>	5.08 Φ mm	0.14 A/W	1000 pF	50 MΩ	2 μs	6 / TO-8	

								
UV-35	35 mm²	6.60 x 5.33 mm	0.14 A/W	1600 pF	30 MΩ	3 μs	6 / TO-8	
UV-50	50 mm²	7.87 F mm	0.14 A/W	2500 pF	20 MΩ	3.5 μs	11 / BNC	
UV-50L‡	50 mm²	7.87 F mm	0.14 A/W	2500 pF	20 MΩ	3.5 μs	10 / Lo-Prof	
UV-100	100 mm²	11.28 Φ mm	0.14 A/W	4500 pF	10 MΩ	5.9 μs	11 / BNC	
UV-100L	100 mm²	11.28 Φ mm	0.14 A/W	4500 pF	10 MΩ	5.9 μs	10 / Lo-Prof	

Inversion Layer, Plastic Package §

Model Number	Active Area	Active Area Dimensions	Responsivity @ 254nm	Capacitance	Shunt Resistance	Rise Time	Package	Click Image to Zoom
FIL-UV005	5.1 mm²	2.54 Φ mm	0.14 A/W	300 pF	200 MΩ	0.9 μs	14 / Plastic	
UV-35P	35 mm²	6.60 x 5.33 mm	0.14 A/W	1600 pF	---	3 μs	25 / Plastic	
FIL-UV50	50 mm²	7.87 Φ mm	0.14 A/W	2500 pF	20 MΩ	3.5 μs	15 / Plastic	

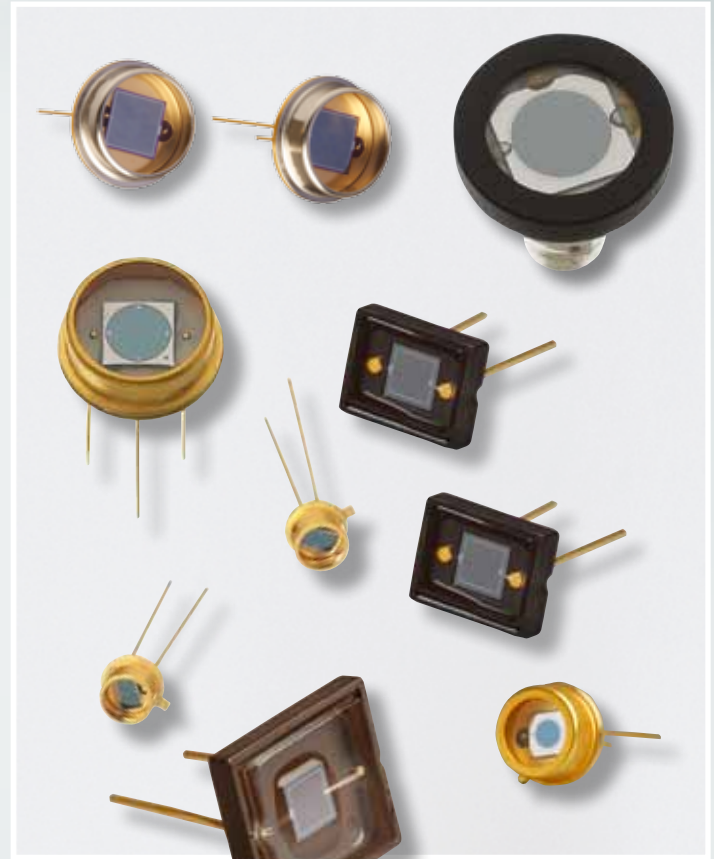
‡ The 'l' suffix on the model number is indicative of the photodiode chip being isolated from the the package by an additional pin connected to the case.  
§ The photodiode chips in "FIL" series are isolated in a low profile plastic package. They have a large field of view as well as "in line" pins.

OSI Optoelectronics offers two distinct families of UV enhanced silicon photodiodes. Inversion channel series and planar diffused series. Both families of devices are especially designed for low noise detection in the UV region of electromagnetic spectrum.

Inversion layer structure UV enhanced photodiodes exhibit 100% internal quantum efficiency and are well suited for low intensity light measurements. They have high shunt resistance, low noise and high breakdown voltages. The response uniformity across the surface and quantum efficiency improves with 5 to 10 volts applied reverse bias. In photovoltaic mode (unbiased), the capacitance is higher than diffused devices but decreases rapidly with an applied reverse bias. Photocurrent non-linearity sets in at lower photocurrents for inversion layer devices compared to the diffused ones. Below 700nm, their responsivities vary little with temperature.

Planar diffused structure UV enhanced photodiodes show significant advantages over inversion layer devices, such as lower capacitance and higher response time. These devices exhibit linearity of photocurrent up to higher light input power compared to inversion layer devices. They have relatively lower responsivities and quantum efficiencies compared to inversion layer devices

There are two types of planar diffused UV enhanced photodiodes available: UVDQ and UVEQ. Both series have almost similar electro-optical characteristics, except in the UVEQ series, where the near IR responses of the devices are suppressed. This is especially desirable if blocking the near IR region of the spectrum is necessary. UVDQ devices peak at 970 nm and UVEQ devices at 720 nm (see graph). Both series may be biased for lower capacitance, faster response and wider dynamic range. Or they may be operated in the photovoltaic (unbiased) mode for applications requiring low drift with temperature variations. The UVEQ devices have a higher shunt resistance than their counterparts of UVDQ devices, but have a higher capacitance.



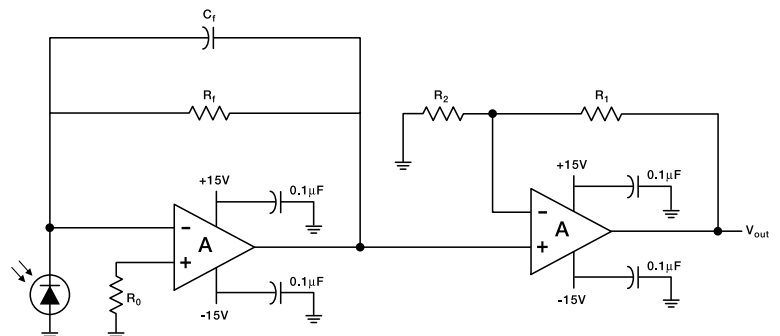
### APPLICATIONS

- Pollution Monitoring
- Medical Instrumentation
- UV Exposure Meters
- Spectroscopy
- Water Purification
- Fluorescence

### FEATURES

- Inversion series:
  - 100% Internal QE
- Ultra High  $R_{SH}$
- Planar Diffused Series:
  - IR Suppressed
  - High Speed Response
  - High Stability
- Excellent UV response

These detectors are ideal for coupling to an OP-AMP in the current mode configuration as shown.



# Inversion Layer UV Enhanced Photodiodes

Typical Electro-Optical Specifications at  $T_A=23^{\circ}\text{C}$

Model Number	Active Area		Responsivity (A/W)		Capacitance (pF)	Shunt Resistance (MΩ)		NEP (W/√Hz)	Reverse Voltage (V)	Rise Time (μs)	Operating Current (mA)	Temp.* Range (°C)		Package Style ¶
	Area (mm²)	Dimensions (mm)	254 nm		0 V	-10 mV		0V 254 nm		0 V 254 nm 50 Ω	0 V	Operating	Storage	
			min.	typ.	max.	min.	typ.	typ.	max.	typ.	typ.			

## 'UV Enhanced' Series, Inversion Layer, Metal Package

UV-001«	0.8	1.0 ϕ	0.09	0.14	60	250	500	6.4 e-14	5	0.2	0.1	-20 ~ +60	-55 ~ +80	5 / TO-5							
UV-005	5.1	2.54 ϕ			300	80	200	1.0 e-13		0.9											
UV-015	15	3.05 x 3.81			800	30	100	1.4 e-13		2.0											
UV-20	20	5.08 ϕ			1000	25	50	2.0 e-13		2.0											
UV-35	35	6.60 x 5.33			1600	20	30	1.7 e-13		3.0		-10 ~ +60	-20 ~ +70	6 / TO-8							
UV-50	50	7.87 ϕ			2500	10	20	2.6 e-13		3.5											
UV-50L ‡																					
UV-100	100	11.28 ϕ			4500	5	10	4.5 e-13		5.9											
UV-100L										10 / Lo-Prof											

## 'UV Enhanced' Series, Inversion Layer, Plastic Package §

<b>UV-35P</b>	35	6.60 x 5.33	0.09	0.14	1600	15	30	1.7 e-13	5	3.0	0.1	-10 ~ +60	-20 ~ +70	25 / Plastic
<b>FIL-UV50</b>	50	7.87 $\phi$			2500	10	20	2.1 e-13		3.5				15 / Plastic

‡ The 'L' suffix on the model number is indicative of the photodiode chip being isolated from the package by an additional pin connected to the case.

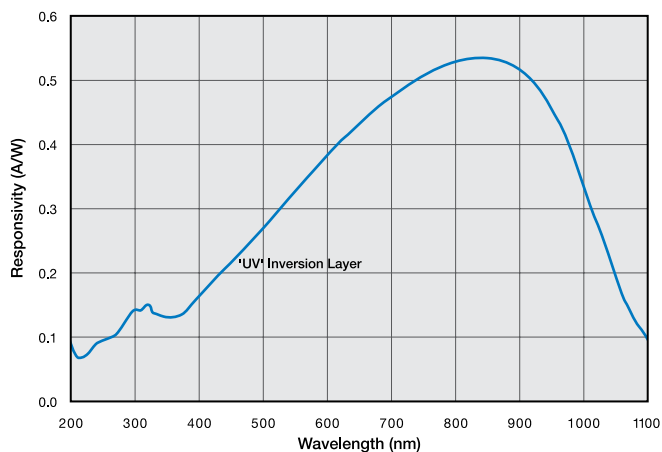
§ The photodiode chips in "FIL" series are isolated in a low profile plastic package. They have a large field of view as well as in line pins.

¶ For mechanical drawings please refer to pages 61 thru 73.

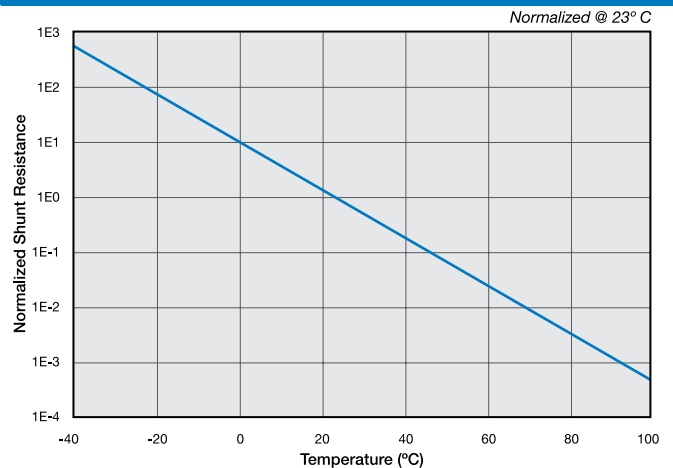
\* Non-Condensing temperature and Storage Range, Non-Condensing Environment.

« Minimum order quantities apply

## Typical Spectral Response



## Typical Shunt Resistance vs. Temperature



## AVOID DIRECT LIGHT

Since the spectral response of silicon photodiode includes the visible light region, care must be taken to avoid photodiode exposure to high ambient light levels, particularly from tungsten sources or sunlight. During shipment from OSI Optoelectronics, your photodiodes are packaged in opaque, padded containers to avoid ambient light exposure and damage due to shock from dropping or jarring.

## AVOID SHARP PHYSICAL SHOCK

Photodiodes can be rendered inoperable if dropped or sharply jarred. The wire bonds are delicate and can become separated from the photodiode's bonding pads when the detector is dropped or otherwise receives a sharp physical blow.

## CLEAN WINDOWS WITH OPTICAL GRADE CLOTH / TISSUE

Most windows on OSI Optoelectronics photodiodes are either silicon or quartz. They should be cleaned with isopropyl alcohol and a soft (optical grade) pad.

## OBSERVE STORAGE TEMPERATURES AND HUMIDITY LEVELS

Photodiode exposure to extreme high or low storage temperatures can affect the subsequent performance of a silicon photodiode. Storage temperature guidelines are presented in the photodiode performance specifications of this catalog. Please maintain a non-condensing environment for optimum performance and lifetime.

## OBSERVE ELECTROSTATIC DISCHARGE (ESD) PRECAUTIONS

OSI Optoelectronics photodiodes, especially with IC devices (e.g. Photops) are considered ESD sensitive. The photodiodes are shipped in ESD protective packaging. When unpacking and using these products, anti-ESD precautions should be observed.

## DO NOT EXPOSE PHOTODIODES TO HARSH CHEMICALS

Photodiode packages and/or operation may be impaired if exposed to CHLOROTHENE, THINNER, ACETONE, or TRICHLOROETHYLENE.

## INSTALL WITH CARE

Most photodiodes in this catalog are provided with wire or pin leads for installation in circuit boards or sockets. Observe the soldering temperatures and conditions specified below:

Soldering Iron:	Soldering 30 W or less Temperature at tip of iron 300°C or lower.	
Dip Soldering:	Bath Temperature:	260±5°C.
	Immersion Time:	within 5 Sec.
	Soldering Time:	within 3 Sec.
Vapor Phase Soldering:	DO NOT USE	
Reflow Soldering:	DO NOT USE	

Photodiodes in plastic packages should be given special care. Clear plastic packages are more sensitive to environmental stress than those of black plastic. Storing devices in high humidity can present problems when soldering. Since the rapid heating during soldering stresses the wire bonds and can cause wire to bonding pad separation, it is recommended that devices in plastic packages to be baked for 24 hours at 85°C.

The leads on the photodiode **SHOULD NOT BE FORMED**. If your application requires lead spacing modification, please contact OSI Optoelectronics Applications group at (310)978-0516 before forming a product's leads. Product warranties could be voided.



\*Most of our standard catalog products are RoHS Compliant. Please contact us for details

# Mechanical Drawings

Mechanical Specifications and Die Topography

## 1. Parameter Definitions:

A = Distance from top of chip to top of glass.

a = Photodiode Anode.

B = Distance from top of glass to bottom of case.

c = Photodiode Cathode

(Note: cathode is common to case in metal package products unless otherwise noted).

W = Window Diameter.

F.O.V. = Field of View (see definition below).

## 2. Dimensions are in inches (1 inch = 25.4 mm).

## 3. Pin diameters are $0.018 \pm 0.002$ " unless otherwise specified.

## 4. Tolerances (unless otherwise noted)

General:  $0.XX \pm 0.01$ "

$0.XXX \pm 0.005$ "

Chip Centering:  $\pm 0.010$ "

Dimension 'A':  $\pm 0.015$ "

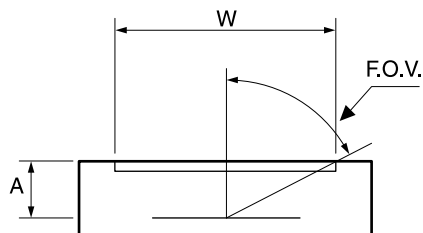
## 5. Windows

All '**UV**' Enhanced products are provided with QUARTZ glass windows,  $0.027 \pm 0.002$ " thick.

All '**XUV**' products are provided with removable windows.

All '**DLS**' PSD products are provided with A/R coated glass windows.

All '**FIL**' photoconductive and photovoltaic products are epoxy filled instead of glass windows.



$$F.O.V. = \tan^{-1} \left( \frac{W}{2A} \right)$$

**OSI Optoelectronics**  
An OSI Systems Company



For Further Assistance  
Please Call One of Our Experienced  
Sales and Applications Engineers

**310-978-0516**



- Or -  
visit our website at  
**[www.osioptoelectronics.com](http://www.osioptoelectronics.com)**

# Mechanical Specifications

All units in inches. Pinouts are bottom view.

1 TO-18		2 TO-5		3 TO-8																																	
<p>Pin Circle Dia.=0.100</p> <table border="1"><thead><tr><th>P/N</th><th>A</th><th>B</th><th>W</th></tr></thead><tbody><tr><td>PIN-020A</td><td>0.075</td><td>0.200</td><td>0.155</td></tr><tr><td>PIN-040A</td><td>0.075</td><td>0.200</td><td>0.155</td></tr></tbody></table>		P/N	A	B	W	PIN-020A	0.075	0.200	0.155	PIN-040A	0.075	0.200	0.155	<p>Pin Circle Dia.=0.200</p> <table border="1"><thead><tr><th>P/N</th><th>A</th><th>B</th><th>W</th></tr></thead><tbody><tr><td>All Others</td><td>0.094</td><td>0.180</td><td>0.240</td></tr><tr><td>CD-25T</td><td>0.050</td><td>0.130</td><td>0.23</td></tr></tbody></table>		P/N	A	B	W	All Others	0.094	0.180	0.240	CD-25T	0.050	0.130	0.23	<p>Pin Circle Dia.=0.295</p> <table border="1"><thead><tr><th>P/N</th><th>A</th></tr></thead><tbody><tr><td>PIN-6DI/6DPI APD50-8-150-T08</td><td>0.115</td></tr><tr><td>PIN-44DI/44DPI</td><td>0.125</td></tr><tr><td>OSD35-0</td><td>0.130</td></tr></tbody></table>		P/N	A	PIN-6DI/6DPI APD50-8-150-T08	0.115	PIN-44DI/44DPI	0.125	OSD35-0	0.130
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Products: PIN-020A PIN-040A PIN-040-DP/SB		Products: PIN-5DI PIN-5DPI PIN-13DI PIN-13DPI PIN-5-YAG CD-25T		Products: PIN-6DI PIN-6DPI PIN-44DI PIN-44DPI APD50-8-150-T08																																	

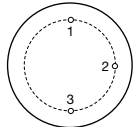
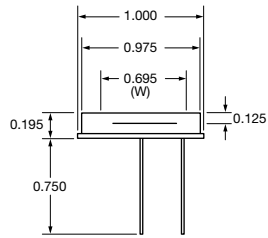
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7 TO-18		8 TO-18		9 TO-18													
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Products: PIN-3CD PIN-3CDP BPX-65 OSD1-0 OSD1-5T OSD3-5T OSD1-E OSD3-E		Products: PIN-125DPL		Products: PIN-HR005 PIN-HR008 PIN-HR020 PIN-HR026 PIN-HR040													

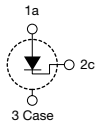
# Mechanical Specifications

All units in inches. Pinouts are bottom view.

## 10 Low Profile



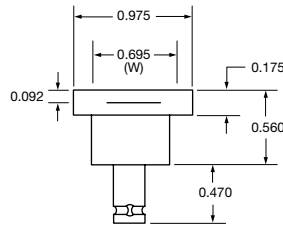
Pin Circle Dia.=0.73



### Products:

PIN-10DI  
PIN-10DPI  
PIN-10DPI/SB  
UV-50L  
UV-100L

## 11 BNC

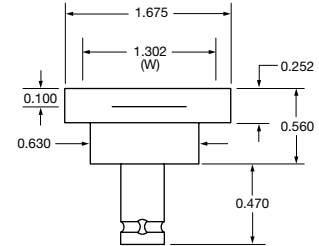


Outer Contact — Anode	PIN-10D, PIN-10DP, PIN-10DP/SB UV-100DQ, UV-100EQ
Outer Contact — Cathode	UV-50, UV-100

### Products:

PIN-10D  
PIN-10DP  
PIN-10DP/SB  
UV-50  
UV-100  
UV-100DQ  
UV-100EQ

## 12 BNC

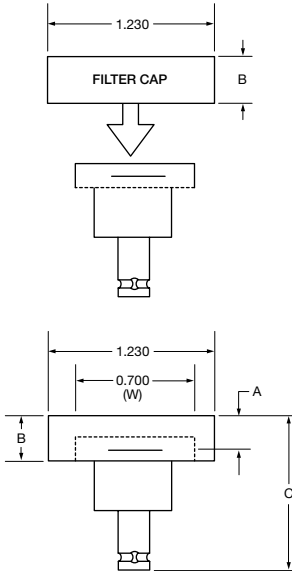


Outer Contact — Anode

### Products:

PIN-25D  
PIN-25DP

## 13 Special BNC

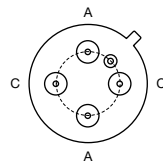
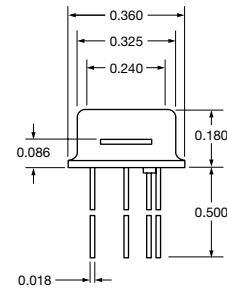


Dimensions			
P/N	A	B	C
PIN-10DF	0.217	0.330	1.020
PIN-10AP	0.386	0.550	1.415

### Products:

PIN-10AP  
PIN-10DF

## 14 TO-5

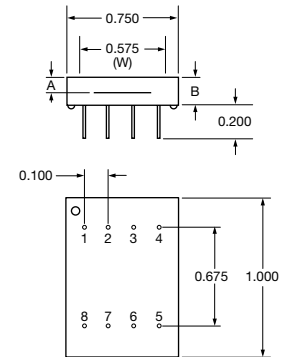


Pin Circle Dia.= 0.200  
Bottom View

### Products:

DLS-2S

## 15 Special Plastic



Dimensions		
P/N	A	B
FIL-UV50	0.090	0.155

Pinouts							
P/N	1	2	3	4	5	6	7
FIL-UV50	c	-	-	a	c	-	a

### Products:

FIL-UV50

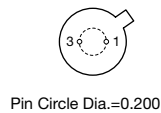
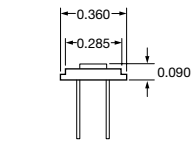
# Mechanical Specifications

All units in inches. Pinouts are bottom view.

## 22 TO-5

Products:

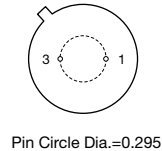
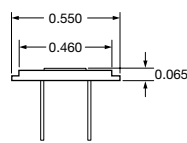
XUV-005



## 23 TO-8

Products:

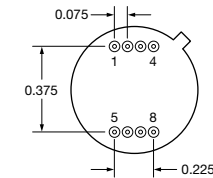
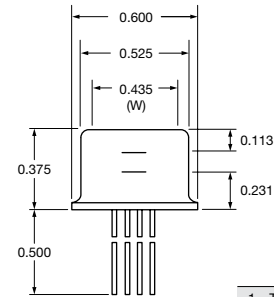
XUV-020  
XUV-035



## 24 TO-8

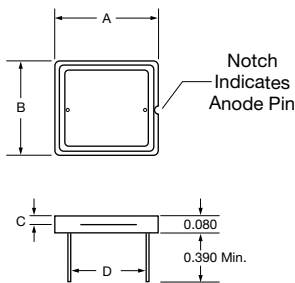
Products:

PIN-DSIn-TEC



Pinout	
1	TEC (-)
2	Thermistor
3	Thermistor
4	TEC (+)
5	Top Silicon, Cathode
6	Top Silicon, Anode
7	Bottom InGaAs, Anode
8	Bottom InGaAs, Cathode

## 25 Special Ceramic / Plastic



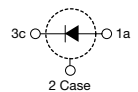
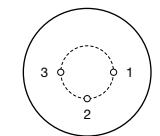
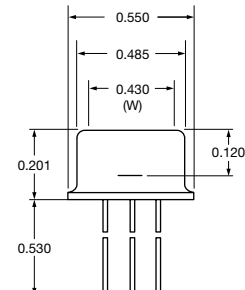
P/N	Dimensions			
	A	B	C	D
UV-005EQC	0.300	0.236	0.024	0.177
UV-035EQC	0.400	0.350	0.028	0.290
UV-100EQC	0.650	0.590	0.028	0.490
UV-005DQC	0.300	0.236	0.035	0.177
UV-035DQC	0.400	0.350	0.039	0.290
UV-100DQC	0.650	0.590	0.039	0.490
XUV-50C	0.650	0.590	0.027	0.490
XUV-100C	0.650	0.590	0.027	0.490
RD-100	0.650	0.590	0.027	0.490
RD-100A	0.650	0.590	0.027	0.490
UV-35P	0.390	0.345	0.050	0.275
OSD35-LR-A	0.390	0.350	---	0.290
OSD35-LR-D	0.390	0.350	---	0.290

Note: OSD35-prefix packages come with 0.31" (min.) leads

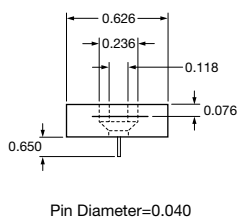
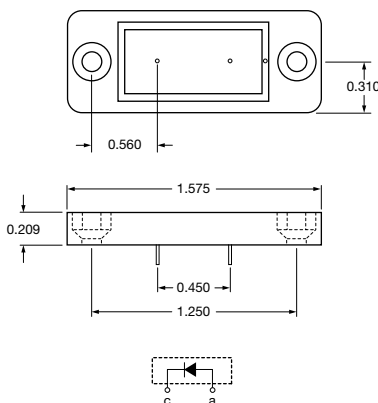
## 26 TO-8

Products:

RD-100  
RD-100A  
UV-35P  
UV-005EQC  
UV-035EQC  
UV-100EQC  
UV-005DQC  
UV-035DQC  
UV-100DQC  
XUV-50C  
XUV-100C  
OSD35-LR-A  
OSD35-LR-D



## 27 Special Plastic



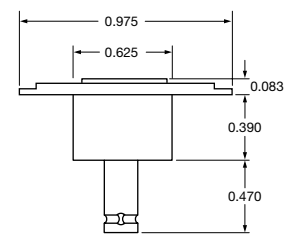
## 28 BNC

Products:

PIN-220D  
PIN-220DP  
PIN-220DP/SB

Products:

XUV-100



BNC Connector  
Outer Contact = Cathode